

JFET Input Operational Amplifiers

These low–cost JFET input operational amplifiers combine two state–of–the–art linear technologies on a single monolithic integrated circuit. Each internally compensated operational amplifier has well matched high voltage JFET input devices for low input offset voltage. The BIFET technology provides wide bandwidths and fast slew rates with low input bias currents, input offset currents, and supply currents.

These devices are available in single, dual and quad operational amplifiers which are pin-compatible with the industry standard MC1741, MC1458, and the MC3403/LM324 bipolar products.

• Input Offset Voltage Options of 6.0 mV and 15 mV Max

Low Input Bias Current: 30 pA
Low Input Offset Current: 5.0 pA
Wide Gain Bandwidth: 4.0 MHz

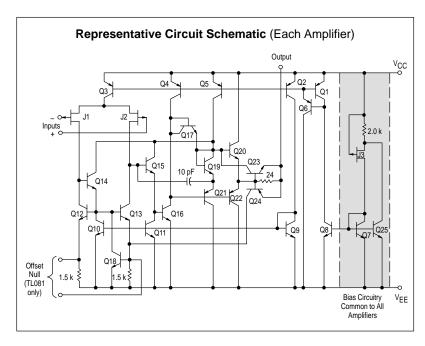
High Slew Rate: 13 V/μs

• Low Supply Current: 1.4 mA per Amplifier

High Input Impedance: 10¹² Ω

ORDERING INFORMATION

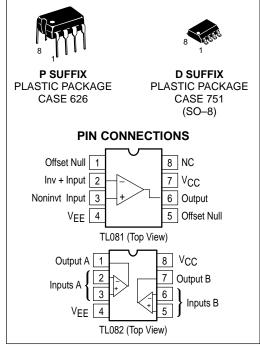
Op Amp Function	Device	Operating Temperature Range	Package
Single	TL081CD	T _A = 0° to +70°C	SO-8
Single	TL081ACP	1A=0 10+70 C	Plastic DIP
Dual	TL082CD	$T_A = 0^{\circ} \text{ to } +70^{\circ}\text{C}$	SO-8
Duai	TL082ACP	1A=0 10+70 C	Plastic DIP
Quad	TL084CN, ACN	$T_A = 0^\circ \text{ to } +70^\circ \text{C}$	Plastic DIP

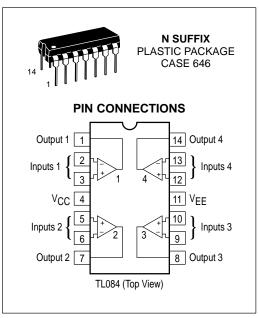


TL081C,AC TL082C,AC TL084C,AC

JFET INPUT OPERATIONAL AMPLIFIERS

SEMICONDUCTOR TECHNICAL DATA





MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Supply Voltage	V _{CC}	18 –18	V
Differential Input Voltage	V _{ID}	±30	V
Input Voltage Range (Note 1)	VIDR	±15	V
Output Short Circuit Duration (Note 2)	tsc	Continuous	
Power Dissipation Plastic Package (N, P) Derate above T _A = +47°C	P _D 1/θJA	680 10	mW mW/°C
Operating Ambient Temperature Range	TA	0 to +70	°C
Storage Temperature Range	T _{stg}	-65 to +150	°C

NOTES: 1. The magnitude of the input voltage must not exceed the magnitude of the supply voltage or 15 V, whichever is less.

ELECTRICAL CHARACTERISTICS ($V_{CC} = 15 \text{ V}, V_{EE} = -15 \text{ V}, T_A = T_{low} \text{ to } T_{high} \text{ [Note 1].)}$

Characteristics	Symbol	Min	Тур	Max	Unit
Input Offset Voltage (R _S ≤ 10 k, V _{CM} = 0)	V _{IO}				mV
TL081C, TL082C		-	_	20	
TL084C		-	_	20	
TL08_AC		_	-	7.5	
Input Offset Current (V _{CM} = 0) (Note 2)	IIO				nA
TL08_C		-	_	5.0	
TL08_AC		-	-	3.0	
Input Bias Current (V _{CM} = 0) (Note 2)	I _{IB}				nA
TL08_C		-	-	10	
TL08_AC		_	-	7.0	
Large–Signal Voltage Gain (V _O = ±10 V,R _L ≥ 2.0 k)	AVOL				V/mV
TL08_C		15	-	_	
TL08_AC		25	-	_	
Output Voltage Swing (Peak-to-Peak)	Vo				V
$(R_L \ge 10 \text{ k})$		24	_	-	
$(R_L^- \ge 2.0 \text{ k})$		20	_	_	

NOTES: 1. T_{low} = 0°C for TL081AC,C TL082AC,C TL084AC,C TL084AC,C

Figure 1. Unity Gain Voltage Follower

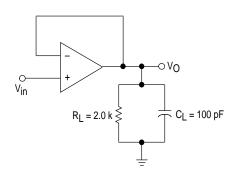
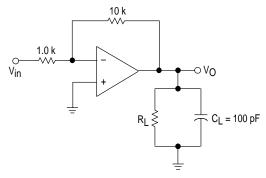


Figure 2. Inverting Gain of 10 Amplifier



The output may be shorted to ground or either supply. Temperature and/or supply voltages must be limited to ensure that power dissipation ratings are not exceeded.

^{3.} ESD data available upon request.

^{2.} Input Bias currents of JFET input op amps approximately double for every 10°C rise in Junction Temperature as shown in Figure 3. To maintain junction temperature as close to ambient temperature as possible, pulse techniques must be used during testing.

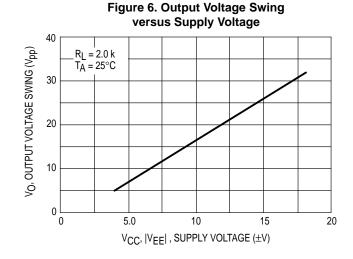
ELECTRICAL CHARACTERISTICS ($V_{CC} = 15 \text{ V}$, $V_{EE} = -15 \text{ V}$, $T_A = 25^{\circ}\text{C}$, unless otherwise noted.)

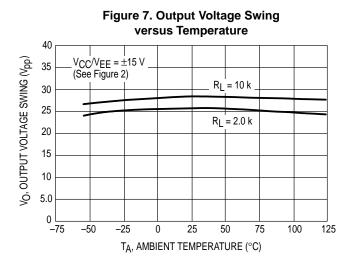
Characteristics	Symbol	Min	Тур	Max	Unit
Input Offset Voltage (Rs \leq 10 k, V _{CM} = 0) TL081C, TL082C TL084C TL08_AC	VIO	- - -	5.0 5.0 3.0	15 15 6.0	mV
Average Temperature Coefficient of Input Offset Voltage $R_S = 50 \Omega$, $T_A = T_{low}$ to T_{high} (Note 1)	ΔV _{IO} /ΔΤ	-	10	_	μV/°C
Input Offset Current (V _{CM} = 0) (Note 2) TL08_C TL08_AC	IIO	_ _	5.0 5.0	200 100	pA
Input Bias Current (V _{CM} = 0) (Note 2) TL08_C TL08_AC	I _{IB}	_ _	30 30	400 200	pA
Input Resistance	rį	_	1012	-	Ω
Common Mode Input Voltage Range TL08_C TL08_AC	VICR	±10 ±11	15, –12 15, –12	_ _	V
Large Signal Voltage Gain ($V_O = \pm 10$ V, $R_L \ge 2.0$ k) TL08_C TL08_AC	AVOL	25 50	150 150	_ _	V/mV
Output Voltage Swing (Peak–to–Peak) (R _L = 10 k)	Vo	24	28	-	V
Common Mode Rejection Ratio (R _S ≤ 10 k) TL08_C TL08_AC	CMRR	70 80	100 100	_ _ _	dB
Supply Voltage Rejection Ratio (R _S ≤ 10 k) TL08_C TL08_AC	PSRR	70 80	100 100	_ _	dB
Supply Current (Each Amplifier)	ΙD	-	1.4	2.8	mA
Unity Gain Bandwidth	BW	-	4.0	_	MHz
Slew Rate (See Figure 1) $V_{in} = 10 \text{ V}, R_L = 2.0 \text{ k}, C_L = 100 \text{ pF}$	SR	_	13	_	V/µs
Rise Time (See Figure 1)	t _r	_	0.1	-	μs
Overshoot ($V_{in} = 20 \text{ mV}$, $R_L = 2.0 \text{ k}$, $C_L = 100 \text{ pF}$)	OS	_	10	_	%
Equivalent Input Noise Voltage $R_S = 100 \Omega$, $f = 1000 Hz$	e _n	_	25	_	nV/√Hz
Channel Separation A _V = 100	CS	_	120	_	dB

NOTES: 1. T_{low} = 0°C for TL081AC,C
TL082AC,C
TL084AC,C
TL084AC,C
TL084AC,C
TL084AC,C
TL084AC,C
2. Input Bias currents of JFET input op amps approximately double for every 10°C rise in Junction Temperature as shown in Figure 3. To maintain junction temperature as close to ambient temperature as possible, pulse techniques must be used during testing.

Figure 4. Output Voltage Swing versus Frequency 35 $R_L = 2.0 \text{ k}$ $T_A = 25^{\circ}\text{C}$ (See Figure 2) VO, OUTPUT VOLTAGE SWING (Vpp) 30 VCC/VEE = 25 20 ±10 V 15 10 ±5.0 V 5.0 0 100 1.0 k 10 k 100 k 1.0 M 10 M f, FREQUENCY (Hz)

Figure 5. Output Voltage Swing versus Load Resistance 40 VO, OUTPUT VOLTAGE SWING (Vpp) $V_{CC}/V_{EE} = \pm 15 \text{ V}$ $T_A = 25^{\circ}\text{C}$ (See Figure 2) 30 20 0.2 2.0 0.1 0.7 1.0 4.0 7.0 10 R_I , LOAD RESISTANCE ($k\Omega$)





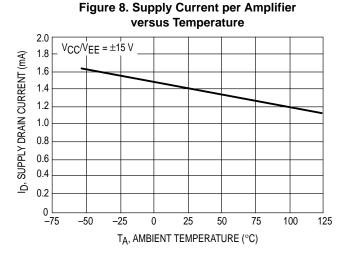
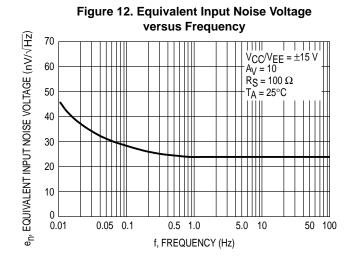


Figure 9. Large Signal Voltage Gain and **Phase Shift versus Frequency** 108 $V_{CC}/V_{EE} = \pm 15 \text{ V}$ $R_{L} = 2.0 \text{ k}$ 107 AVOL, OPEN-LOOP GAIN (V/m/v) PHASE SHIFT (DEGREES) $T_A = 25^{\circ}C$ 106 105 104 Gain 103 45° 102 90° Phase Shift 135° 101 180° 1.0 10 100 10 k 100 k 1.0 M 10 M 100 M f, FREQUENCY (Hz)

Figure 10. Large Signal Voltage Gain versus Temperature 1000 VCC/VEE = ±15 V = VO = ±10 V = RL = 2.0 k = _ AVOL, OPEN-LOOP GAIN (V/m/v) 100 10 1.0 -100 -75 -50 0 25 50 75 TA, AMBIENT TEMPERATURE (°C)

Figure 11. Normalized Slew Rate versus Temperature 1.20 1.15 NORMALIZED SLEW RATE 1.10 1.05 1.0 0.95 0.90 0.85 0.80 75 100 125 -50 50 TA, AMBIENT TEMPERATURE (°C)



versus Frequency THD, TOTAL HARMONIC DISTORTION (%) = V_{CC}/V_{EE} = \pm 15 V 0.5 $A_V = 1.0$ $V_0^{v} = 6.0 \text{ V (RMS)}$ T_A = 25°C 0.05 0.01 0.005 0.001 0.5 50 0.1 1.0 5.0 100 f, FREQUENCY (Hz)

Figure 14. Positive Peak Detector

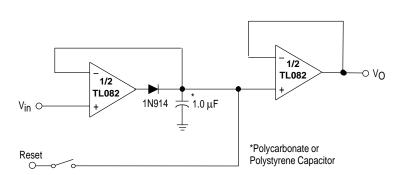


Figure 15. Voltage Controlled Current Source

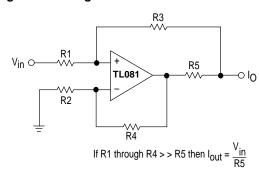
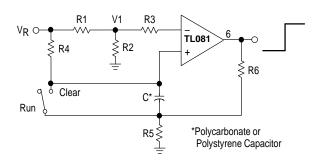
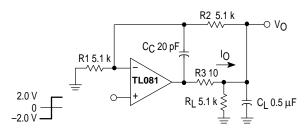


Figure 16. Long Interval RC Timer



Time (t) = R4 C ℓ n (V_R/V_R-V_I), R₃ = R₄, R₅ = 0.1 R₆ If R1 = R2: t = 0.693 R4C

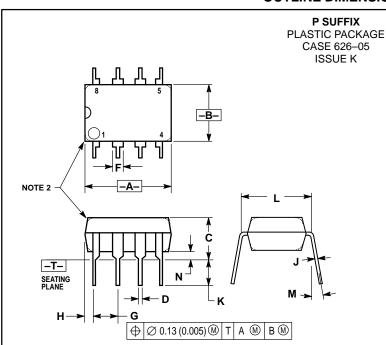
Figure 17. Isolating Large Capacitive Loads



- Overshoot < 10%
- $t_S = 10 \,\mu s$
- When driving large C_L, the V_O slew rate is determined by C_L and I_O(max):

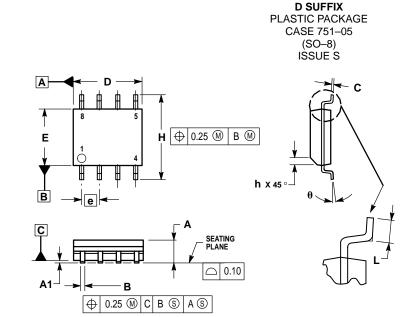
$$\frac{\Delta \text{V}_{\mbox{\scriptsize O}}}{\Delta t} \ = \ \frac{\text{I}_{\mbox{\scriptsize O}}}{\text{C}_{\mbox{\scriptsize L}}} \ \cong \ \frac{0.02}{0.5} \quad \mbox{V/}\mu\mbox{s} = 0.04 \ \mbox{V/}\mu\mbox{s} \ (\mbox{with C}_{\mbox{\scriptsize L}} \ \mbox{shown})$$

OUTLINE DIMENSIONS



- NOTES:
 1. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
 2. PACKAGE CONTOUR OPTIONAL (ROUND OR SQUARE CORNERS).
 3. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	9.40	10.16	0.370	0.400	
В	6.10	6.60	0.240	0.260	
С	3.94	4.45	0.155	0.175	
D	0.38	0.51	0.015	0.020	
F	1.02	1.78	0.040	0.070	
G	2.54	2.54 BSC		0.100 BSC	
Н	0.76	1.27	0.030	0.050	
J	0.20	0.30	0.008	0.012	
K	2.92	3.43	0.115	0.135	
L	7.62 BSC		0.300	BSC	
M		10°		10°	
N	0.76	1.01	0.030	0.040	



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. DIMENSIONS ARE IN MILLIMETERS.

- 2. DIMENSIONS ARE IN MILLIMETERS.
 3. DIMENSION D AND E DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 5. DIMENSION B DOES NOT INCLUDE MOLD PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 TOTAL IN EXCESS OF THE B DIMENSION AT MAXIMUM MATERIAL CONTRICT CONDITION.

	MILLIMETERS			
DIM	MIN	MAX		
Α	1.35	1.75		
A1	0.10	0.25		
В	0.35	0.49		
С	0.18	0.25		
D	4.80	5.00		
Е	3.80	4.00		
е	1.27	BSC		
Н	5.80	6.20		
h	0.25	0.50		
L	0.40	1.25		
θ	0.0	7°		

OUTLINE DIMENSIONS

N SUFFIX PLASTIC PACKAGE CASE 646-06 ISSUE M R -T-SEATING PLANE **D** 14 PL

0.13 (0.005) M

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14 5M 1982
- CONTROLLING DIMENSION: INCH.
- 3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
- DIMENSION B DOES NOT INCLUDE MOLD FLASH.
 ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	18.80
В	0.240	0.260	6.10	6.60
С	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54 BSC	
Н	0.052	0.095	1.32	2.41
۲	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
M		10°		10°
N	0.015	0.039	0.38	1.01

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